



DMP2225L

P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

Low On-Resistance:

$$\begin{split} R_{DS(ON)} < 110 m\Omega & @ V_{GS} = -4.5 V \\ R_{DS(ON)} < 225 m\Omega & @ V_{GS} = -2.5 V \end{split}$$

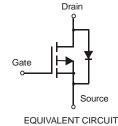
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability

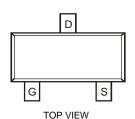
Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)

SOT-23







Maximum Ratings @TA = 25°C unless otherwise specified

Cha	racteristic		Symbol	Value	Units	
Drain-Source Voltage			V_{DSS}	-20	V	
Gate-Source Voltage			V _{GSS}	±12	V	
			I _D	-2.6 -2	А	
Pulsed Drain Current (Note 3)			I _{DM}	8	А	

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P_{D}	1.08	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 1)	$R_{ hetaJA}$	115	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Notes:

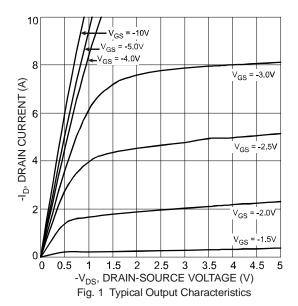
- Device mounted on FR-4 PCB. t ≤5 sec.
- 2. No purposefully added lead.
- $3. \quad \text{Pulse width} \leq \! 10 \mu \text{S, Duty Cycle} \leq \! 1\%.$
- 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

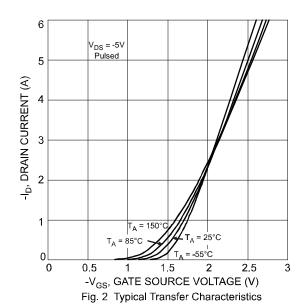


Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)		ē.					
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_		V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_		-800	nA	$V_{DS} = -20V, V_{GS} = 0V$	
On-State Drain Current	1	-6		_	А	$V_{DS} \le -5V$, $V_{GS} = -4.5V$	
On-State Drain Current	I _{D(ON)}	-3	_		^	$V_{DS} \le -5V$, $V_{GS} = -2.5V$	
Gate-Source Leakage	I _{GSS}	_	_	±80	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(th)}$	-0.45		-1.25	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	D	_	80	110	mΩ	$V_{GS} = -4.5V, I_D = -2.6A$	
Static Diain-Source On-Resistance	R _{DS (ON)}		165	225	1112.2	$V_{GS} = -2.5V$, $I_D = -2.0A$	
Forward Transfer Admittance	Y _{fs}	_	4	_	S	$V_{DS} = -5V, I_{D} = -2.6A$	
Diode Forward Voltage (Note 5)	V _{SD}	_	_	-1.26	V	$V_{GS} = 0V, I_S = -2.6A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C _{iss}	_	250	_	pF		
Output Capacitance	Coss	_	88		pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	58	_	pF	1 = 1.0WH IZ	
Gate Resistance	Rg	_	12	16	Ω	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	4.3	5.3		4.5)/.)/ 4.0)/	
Gate-Source Charge	Q _{gs}	_	0.9	_	nC	$V_{GS} = -4.5V, V_{DS} = -10V,$	
Gate-Drain Charge	Q_{gd}	_	2.1	_		$I_D = -2.7A$	

Notes: 5. Short duration pulse test used to minimize self-heating effect.







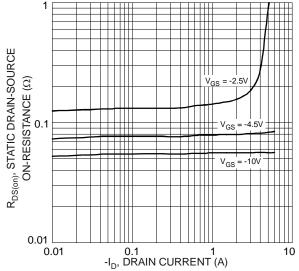


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

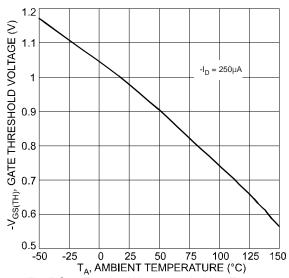


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

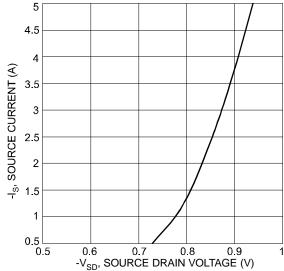
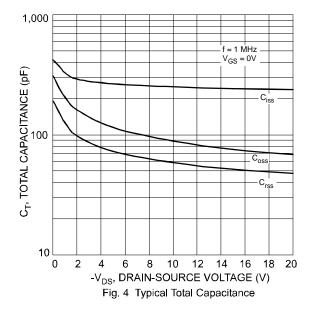


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage



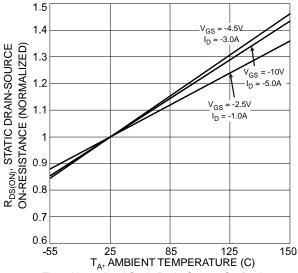


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

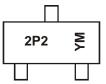


Ordering Information (Note 6)

Part Number	Case	Packaging		
DMP2225L-7	SOT-23	3000/Tape & Reel		

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



2P2 = Product Type Marking Code YM = Date Code Marking

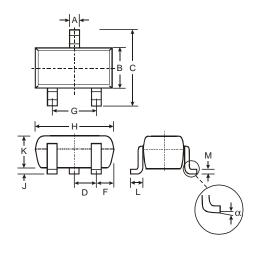
Y = Year (ex: V = 2008)

M = Month (ex: 9 = September)

Date Code Kev

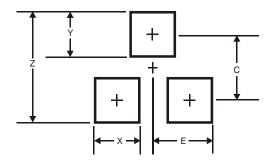
Date Code Ney												
Year	2008		2009	2010)	2011	2012	!	2013	2014		2015
Code	V		W	X		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



SOT-23						
Dim	Min	Max				
Α	0.37	0.51				
В	1.20	1.40				
С	2.30	2.50				
D	0.89	1.03				
F	0.45	0.60				
G	1.78	2.05				
Н	2.80	3.00				
J	0.013	0.10				
K	0.903	1.10				
L	L 0.45 0.6					
M	0.085	0.180				
α	0°	8°				
All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35



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